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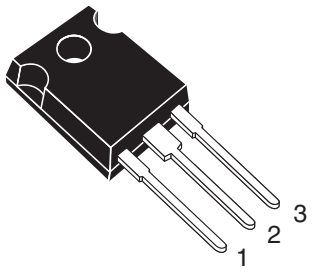
STW12NK90Z

N-channel 900 V, 0.72 Ω, 11 A TO-247 Zener-protected SuperMESH™ Power MOSFET

Features

Order code	V_{DSS}	$R_{DS(on)}$ max	I_D	Pw
STW12NK90Z	900 V	< 0.88 Ω	11 A	230 W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitance
- Very good manufacturing repeatability



TO-247

Application

- Switching applications

Description

This device is made using the SuperMESH™ Power MOSFET technology that is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

Figure 1. Internal schematic diagram

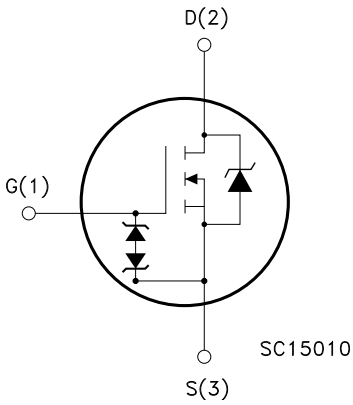


Table 1. Device summary

Order code	Marking	Package	Packaging
STW12NK90Z	W12NK90Z	TO-247	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	900	V
V_{GS}	Gate- source voltage	± 30	V
I_D	Drain current (continuous) at T_C = 25 °C	11	A
I_D	Drain current (continuous) at T_C = 100 °C	7	A
I_{DM} (1)	Drain current (pulsed)	44	A
P_{tot}	Total dissipation at T_C = 25 °C	230	W
	Derating Factor	1.85	W/°C
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100 pF, R=1.5 kΩ)	6000	V
dv/dt (2)	Peak diode recovery voltage slope	4.5	V/ns
T_{stg}	Storage temperature	-55 to 150	°C
T_j	Max. operating junction temperature		

1. Pulse width limited by safe operating area.
2. I_{SD} ≤11 A, di/dt ≤200 A/µs, V_{DD} ≤$V_{(BR)DSS}$, T_j ≤T_{JMAX}.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	0.54	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient max	50	°C/W
T_J	Maximum lead temperature for soldering purpose	300	°C

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	11	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	500	mJ

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} =0	900			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = max rating V_{DS} = max rating, T_C = 125 °C			1 50	µA µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 20 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 100 µA	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10 V, I_D = 5.5 A		0.72	0.88	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} = 15 V, I_D = 5.5 A	-	11		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} = 25 V, f = 1 MHz, V_{GS} = 0	-	3500 280 58		pF pF pF
$C_{oss\ eq}$ (2)	Equivalent output capacitance	V_{GS} = 0, V_{DS} = 0 to 800 V	-	117		pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 450 V, I_D = 5 A R_G = 4.7 Ω V_{GS} = 10 V (see *Figure 14*)	-	31 20 88 55		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 720 V, I_D = 10 A, V_{GS} = 10 V, R_G = 4.7 Ω (see *Figure 15*)	-	113 19 60	152	nC nC nC

1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Coss eq. is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (1)	Source-drain current Source-drain current (pulsed)		-		11 44	A A
V_{SD} (2)	Forward on voltage	I_{SD} = 11 A, V_{GS} = 0	-		1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 10 A,V_{DD} = 50 V di/dt = 100 A/µs, (see *Figure 16*)	-	728 7.8 21.6		ns µC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 10 A, V_{DD} = 50 V di/dt = 100 A/µs, T_j = 150 °C (see *Figure 16*)	-	964 11 23		ns µC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-source breakdown voltage	Igs=± 1 mA (open drain)	30	-		V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

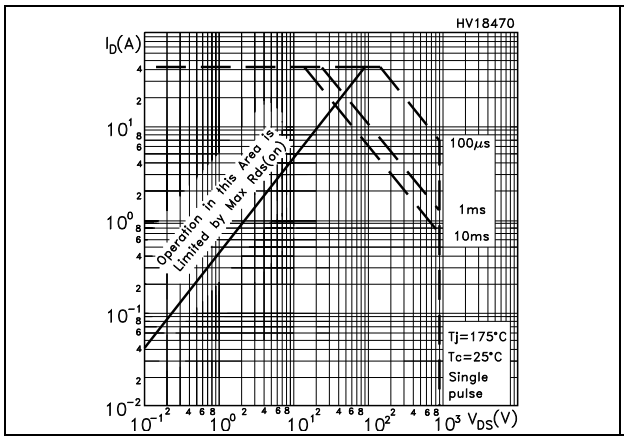


Figure 3. Thermal impedance

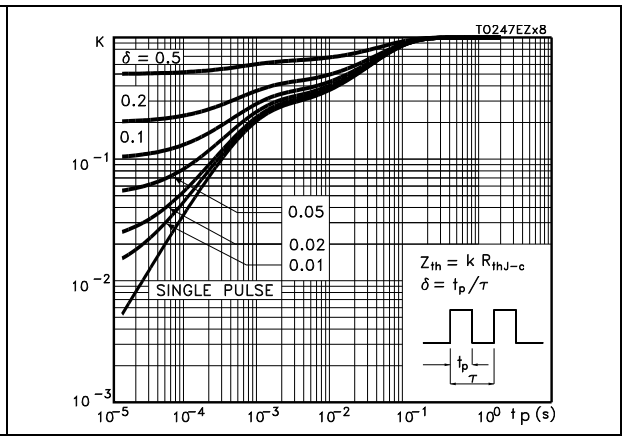


Figure 4. Output characteristics

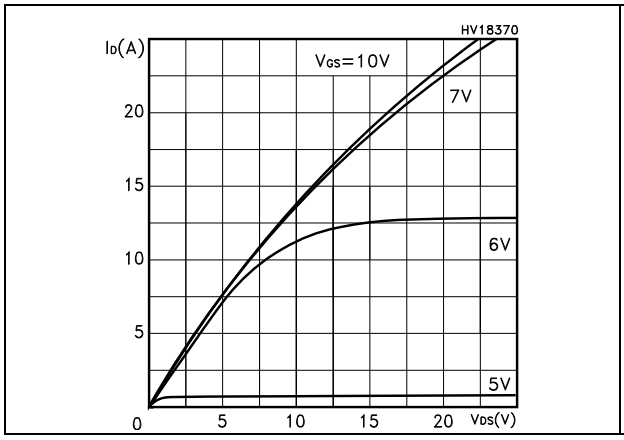


Figure 5. Transfer characteristics

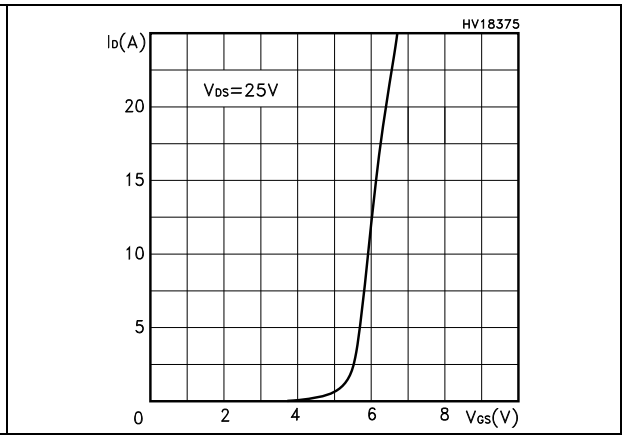


Figure 6. Transconductance

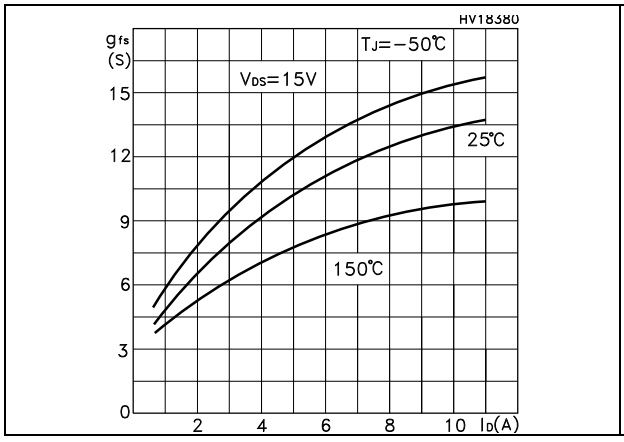


Figure 7. Static drain-source on resistance

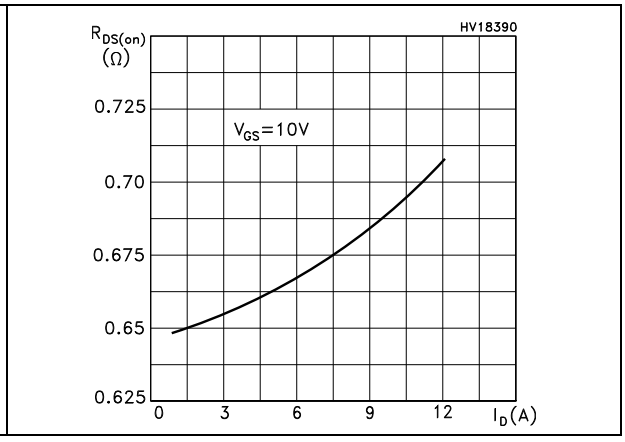


Figure 8. Gate charge vs gate-source voltage

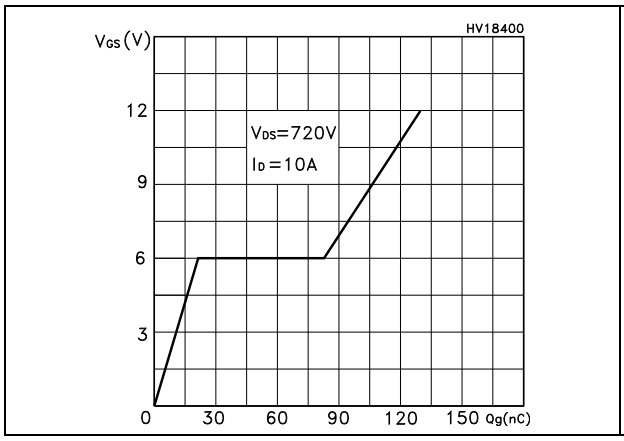


Figure 9. Capacitance variations

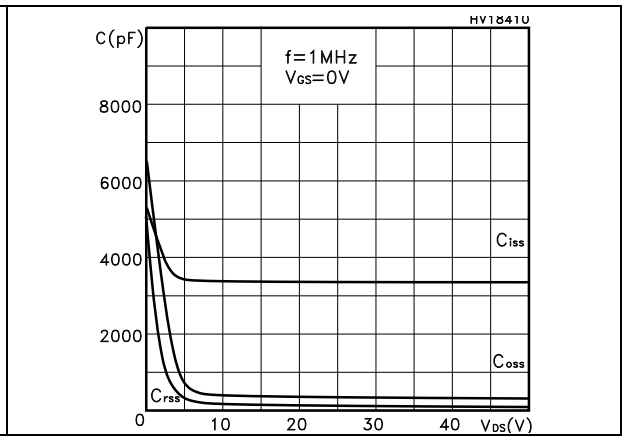


Figure 10. Normalized gate threshold voltage vs temperature

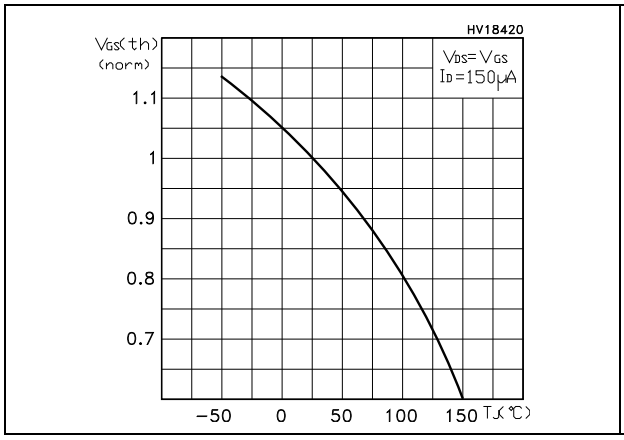


Figure 11. Normalized on resistance vs temperature

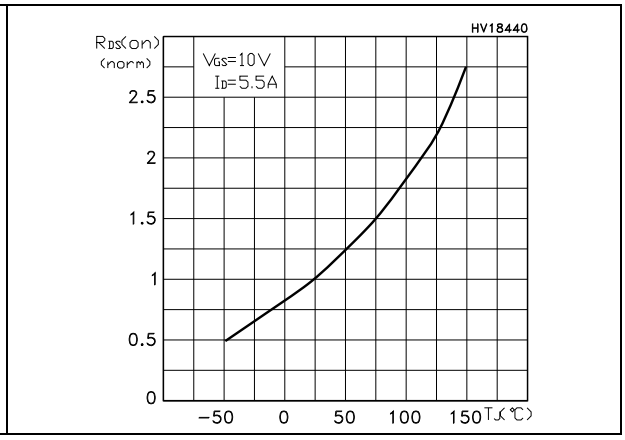


Figure 12. Source-drain diode forward characteristics

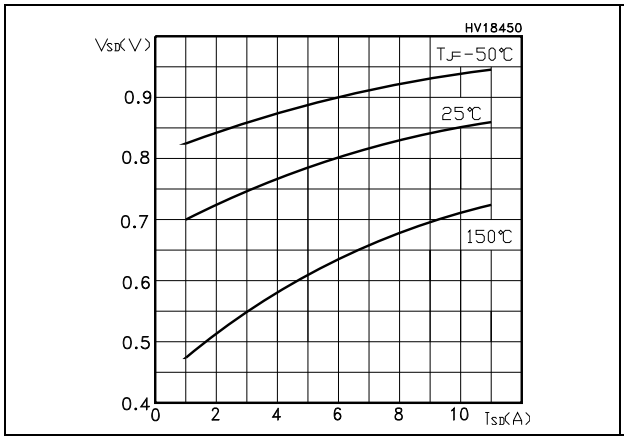
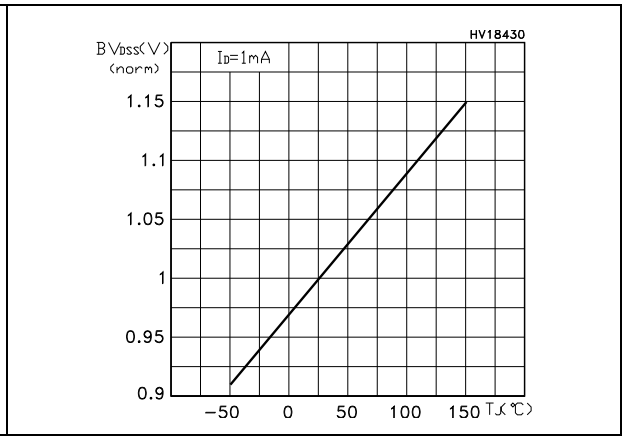


Figure 13. Normalized breakdown voltage vs temperature



3 Test circuits

Figure 14. Switching times test circuit for resistive load

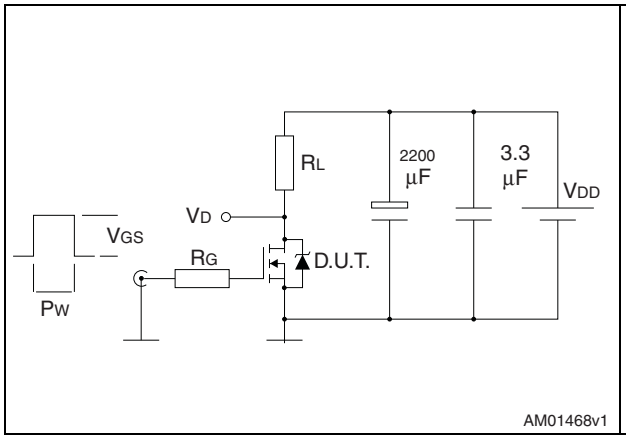


Figure 15. Gate charge test circuit

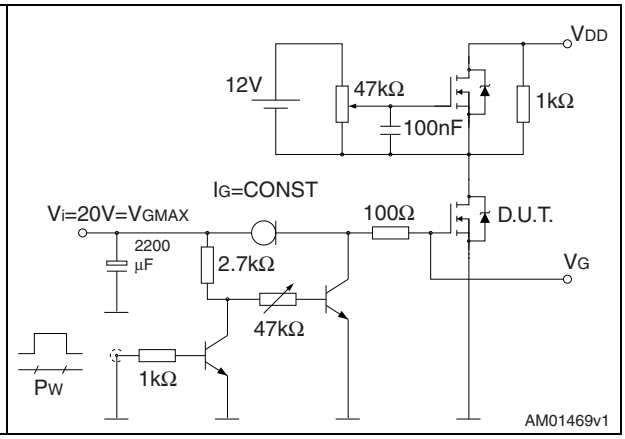


Figure 16. Test circuit for inductive load switching and diode recovery times

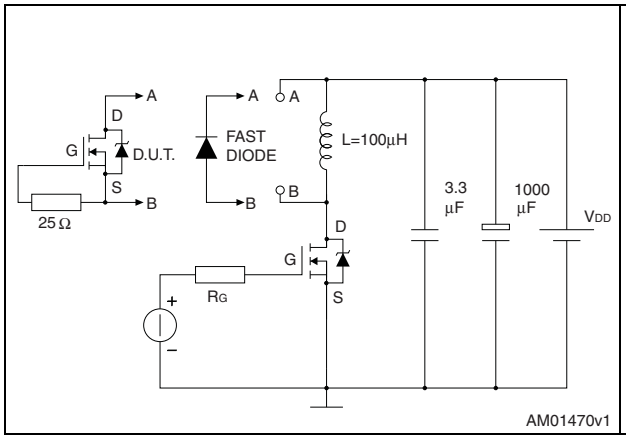


Figure 17. Unclamped Inductive load test circuit

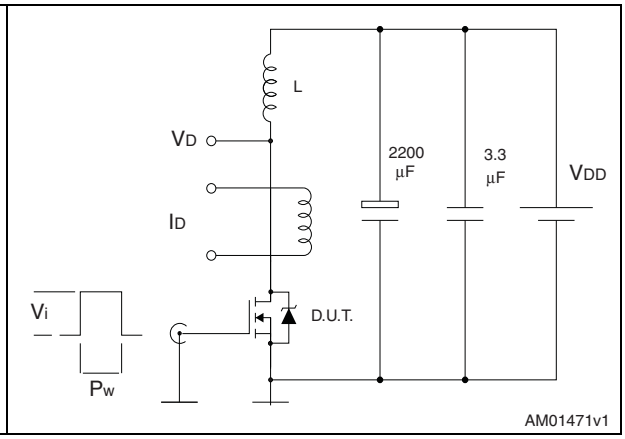


Figure 18. Unclamped inductive waveform

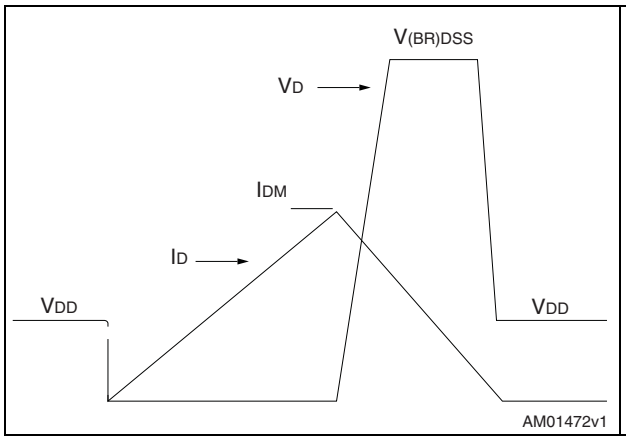
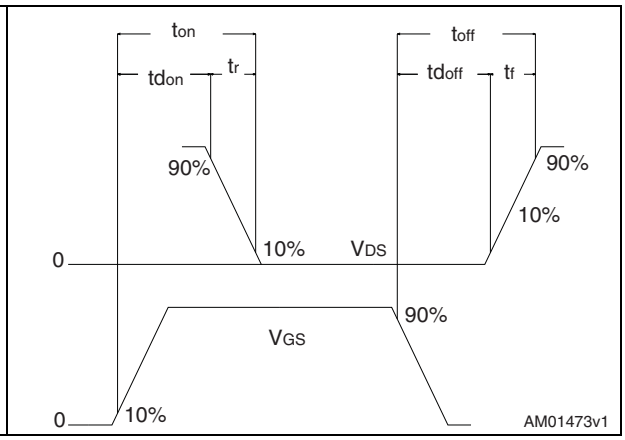


Figure 19. Switching time waveform



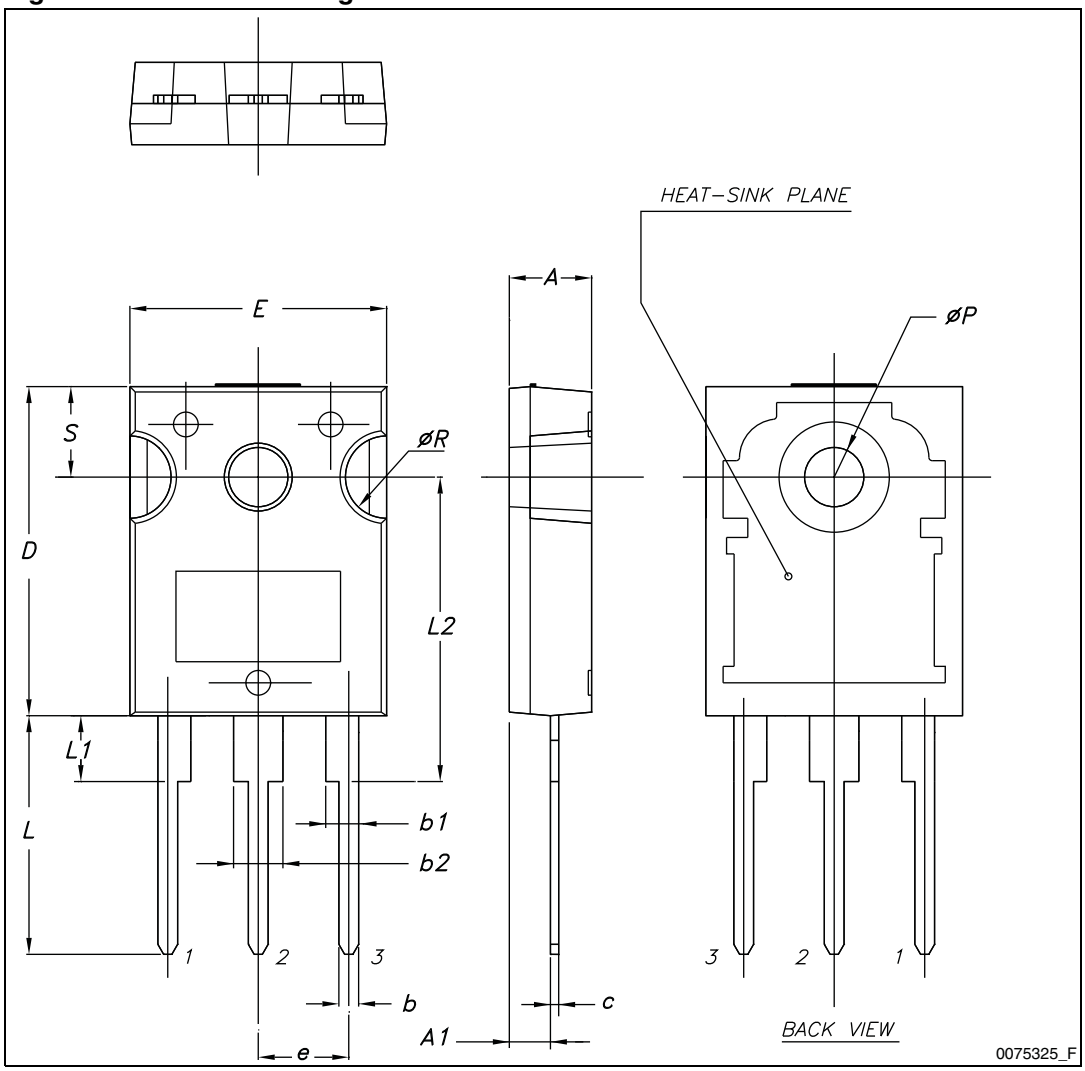
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. TO-247 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
∅P	3.55		3.65
∅R	4.50		5.50
S		5.50	

Figure 20. TO-247 drawing



5 Revision history

Table 10. Document revision history

Date	Revision	Changes
21-Jun-2004	4	Complete version
17-Oct-2006	5	New template, no content change
29-Apr-2011	6	*Table 2: Absolute maximum ratings* has been updated

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